

## FEATURES

- **HIGH POWER**  
P1dB=40.5dBm at 9.5GHz to 10.5GHz
- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH GAIN**  
G1dB=6.0 dB at 9.5 GHz to 10.5GHz
- **HERMETICALLY SEALED PACKAGE**

## RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V f= 9.5 to 10.5GHz	dBm	40.0	40.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	—
Drain Current	IDS1		A	—	4.0	5.0
Power Added Efficiency	$\eta_{add}$		%	—	23	—
Channel Temperature Rise	$\Delta T_{ch}$	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	90

Recommended gate resistance(Rg) : Rg= 100  $\Omega$ (MAX.)

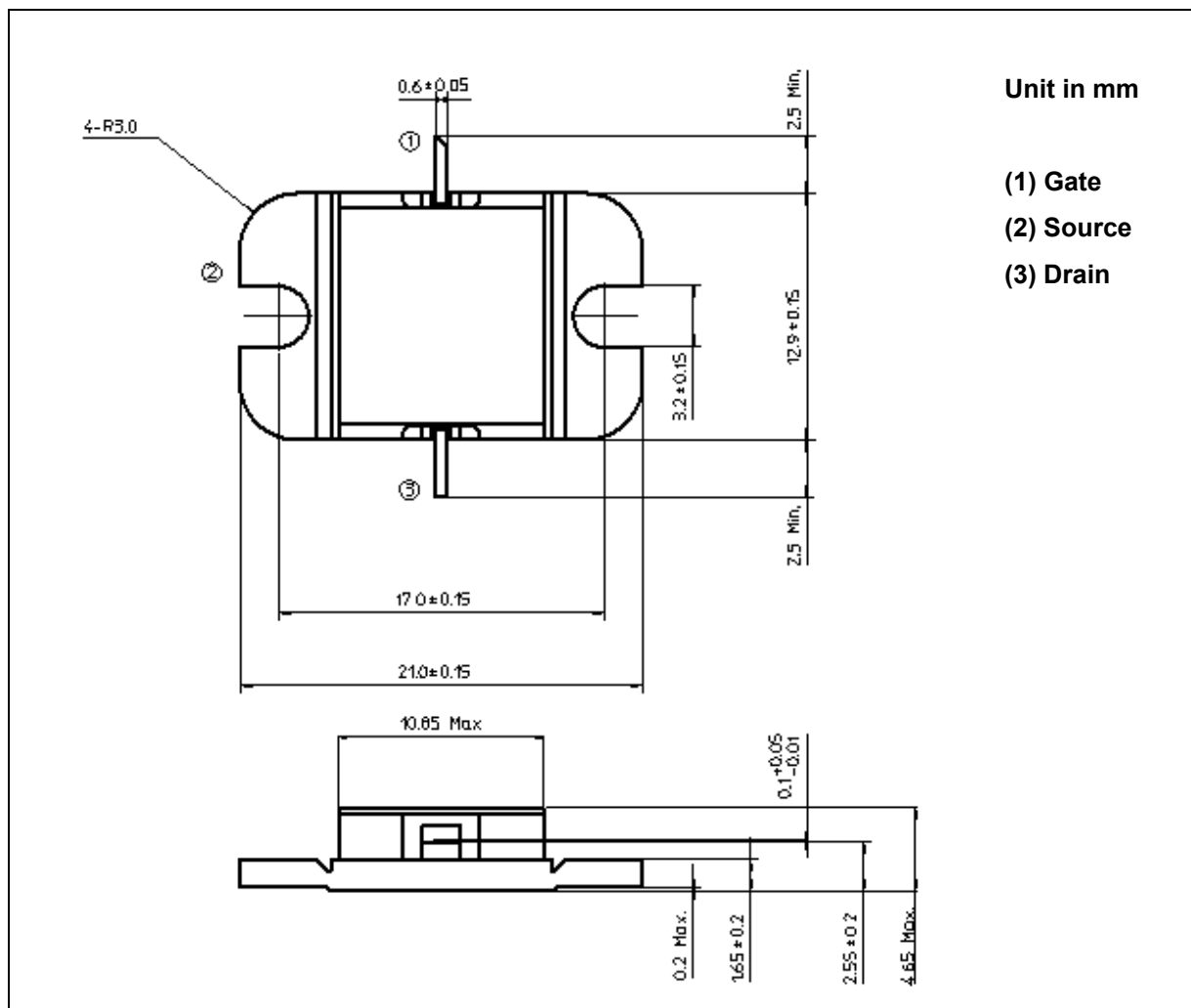
## ELECTRICAL CHARACTERISTICS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	mS	—	3000	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.5	-3.5	-5.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -145 $\mu$ A	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

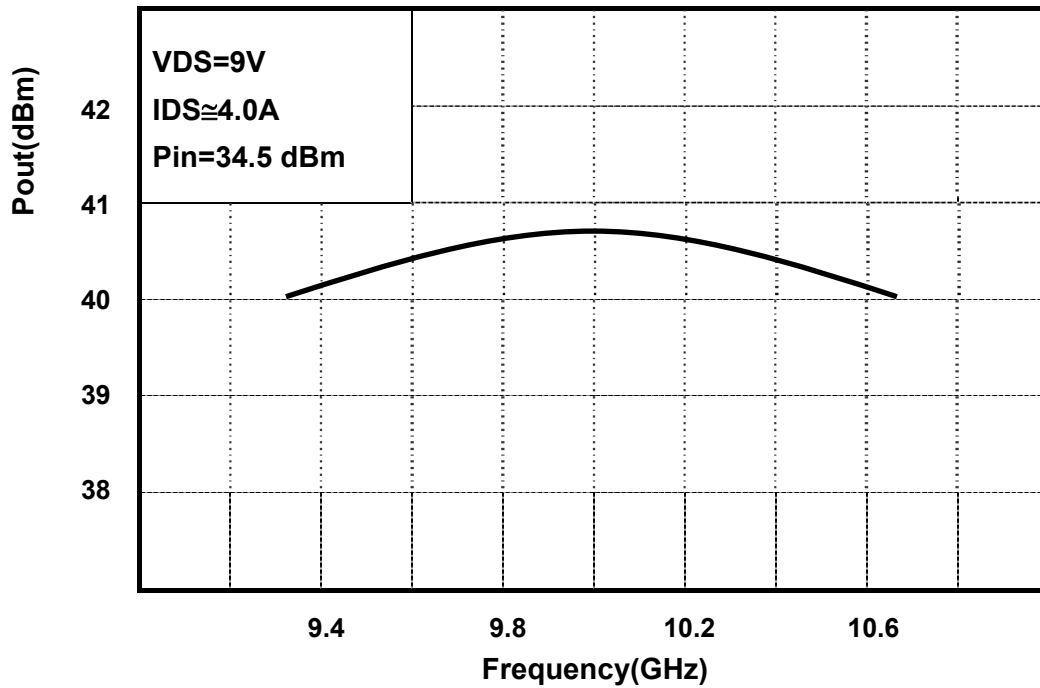
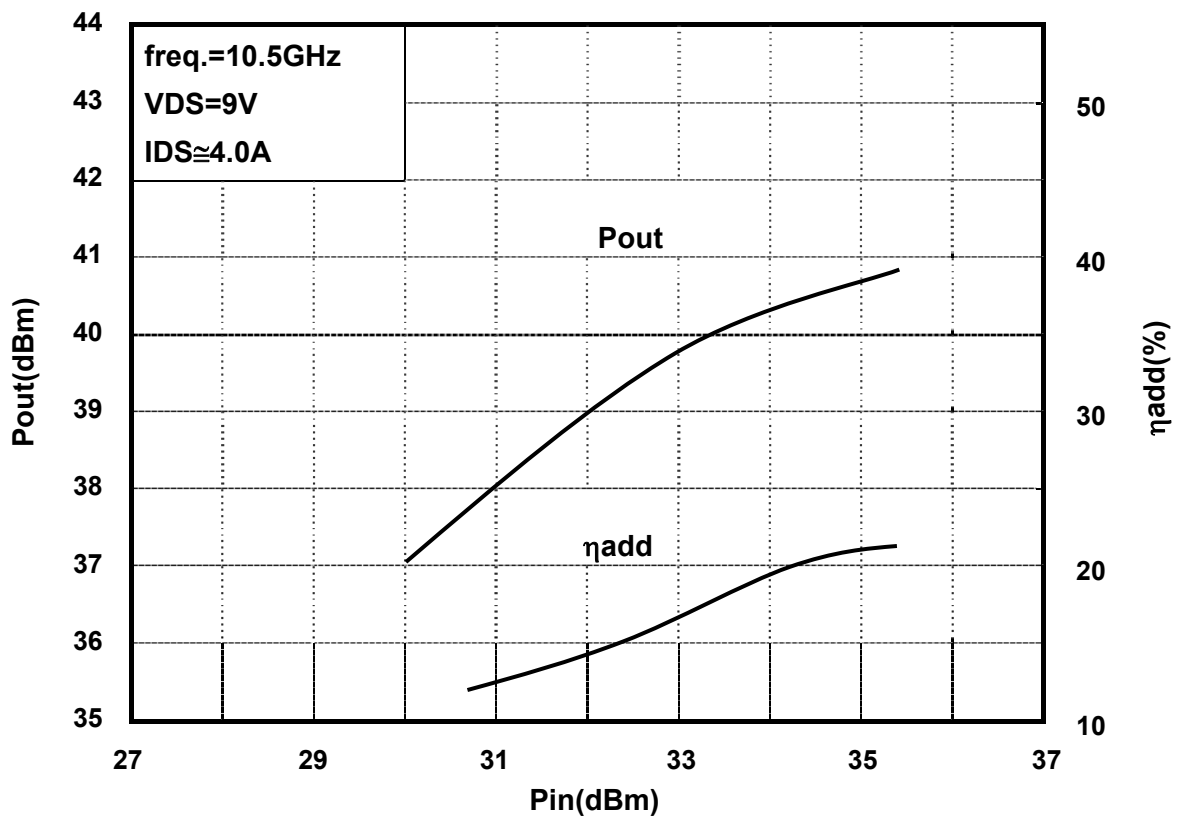
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**ABSOLUTE MAXIMUM RATINGS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	11.5
Total Power Dissipation (Tc= 25 °C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-11C1B)****HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

**RF PERFORMANCE****Output Power (Pout) vs. Frequency****Output Power(Pout) vs. Input Power(Pin)**

**Power Dissipation(PT) vs. Case Temperature(Tc)**